

# Yuewen Sheng

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

41  
papers

1,088  
citations

23  
h-index

31  
g-index

41  
ext. papers

1,394  
ext. citations

12.1  
avg, IF

4.45  
L-index

#	Paper	IF	Citations
41	High-resolution in situ structure determination by cryo-electron tomography and subtomogram averaging using emClarity.. <i>Nature Protocols</i> , <b>2022</b> ,	18.8	3
40	GaS:WS Heterojunctions for Ultrathin Two-Dimensional Photodetectors with Large Linear Dynamic Range across Broad Wavelengths. <i>ACS Nano</i> , <b>2021</b> ,	16.7	7
39	Correlative multi-scale cryo-imaging unveils SARS-CoV-2 assembly and egress. <i>Nature Communications</i> , <b>2021</b> , 12, 4629	17.4	24
38	Transparent ultrathin all-two-dimensional lateral Gr:WS <sub>2</sub> :Gr photodetector arrays on flexible substrates and their strain induced failure mechanisms. <i>Materials Today Advances</i> , <b>2020</b> , 6, 100067	7.4	1
37	Atomic structure and defect dynamics of monolayer lead iodide nanodisks with epitaxial alignment on graphene. <i>Nature Communications</i> , <b>2020</b> , 11, 823	17.4	20
36	Controlling Defects in Continuous 2D GaS Films for High-Performance Wavelength-Tunable UV-Discriminating Photodetectors. <i>Advanced Materials</i> , <b>2020</b> , 32, e1906958	24	24
35	High Photoresponsivity in Ultrathin 2D Lateral Graphene:WS:Graphene Photodetectors Using Direct CVD Growth. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 6421-6430	9.5	52
34	Metal Atom Markers for Imaging Epitaxial Molecular Self-Assembly on Graphene by Scanning Transmission Electron Microscopy. <i>ACS Nano</i> , <b>2019</b> , 13, 7252-7260	16.7	8
33	High-Performance WS Monolayer Light-Emitting Tunneling Devices Using 2D Materials Grown by Chemical Vapor Deposition. <i>ACS Nano</i> , <b>2019</b> , 13, 4530-4537	16.7	34
32	MoS Liquid Cell Electron Microscopy Through Clean and Fast Polymer-Free MoS Transfer. <i>Nano Letters</i> , <b>2019</b> , 19, 1788-1795	11.5	24
31	Morphology Control of Two-Dimensional Tin Disulfide on Transition Metal Dichalcogenides Using Chemical Vapor Deposition for Nanoelectronic Applications. <i>ACS Applied Nano Materials</i> , <b>2019</b> , 2, 4222-4231	5.6	12
30	Postgrowth Substitutional Tin Doping of 2D WS Crystals Using Chemical Vapor Deposition. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 24279-24288	9.5	13
29	Photocurrent Direction Control and Increased Photovoltaic Effects in All-2D Ultrathin Vertical Heterostructures Using Asymmetric h-BN Tunneling Barriers. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 40274-40282	9.5	7
28	Ultrathin All-2D Lateral Graphene/GaS/Graphene UV Photodetectors by Direct CVD Growth. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 48172-48178	9.5	19
27	Direct Laser Patterning and Phase Transformation of 2D PdSe Films for On-Demand Device Fabrication. <i>ACS Nano</i> , <b>2019</b> , 13, 14162-14171	16.7	29
26	Self-Limiting Growth of High-Quality 2D Monolayer MoS <sub>2</sub> by Direct Sulfurization Using Precursor-Soluble Substrates for Advanced Field-Effect Transistors and Photodetectors. <i>ACS Applied Nano Materials</i> , <b>2019</b> , 2, 369-378	5.6	20
25	Symmetry-Controlled Reversible Photovoltaic Current Flow in Ultrathin All 2D Vertically Stacked Graphene/MoS/WS/Graphene Devices. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 2234-2242	9.5	23

24	Revealing Strain-Induced Effects in Ultrathin Heterostructures at the Nanoscale. <i>Nano Letters</i> , <b>2018</b> , 18, 2467-2474	11.5	17
23	Utilizing Interlayer Excitons in Bilayer WS for Increased Photovoltaic Response in Ultrathin Graphene Vertical Cross-Bar Photodetecting Tunneling Transistors. <i>ACS Nano</i> , <b>2018</b> , 12, 4669-4677	16.7	25
22	High-Performance All 2D-Layered Tin Disulfide: Graphene Photodetecting Transistors with Thickness-Controlled Interface Dynamics. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 13002-13010	9.5	23
21	Hydrogen-Assisted Growth of Large-Area Continuous Films of MoS on Monolayer Graphene. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 7304-7314	9.5	36
20	Chemical Vapor Deposition Growth of Two-Dimensional Monolayer Gallium Sulfide Crystals Using Hydrogen Reduction of GaS. <i>ACS Omega</i> , <b>2018</b> , 3, 7897-7903	3.9	24
19	Low-Frequency Noise in Graphene Tunnel Junctions. <i>ACS Nano</i> , <b>2018</b> , 12, 9451-9460	16.7	15
18	Geometrically Enhanced Thermoelectric Effects in Graphene Nanoconstrictions. <i>Nano Letters</i> , <b>2018</b> , 18, 7719-7725	11.5	30
17	2D-Layer-Dependent Behavior in Lateral Au/WS <sub>2</sub> /Graphene Photodiode Devices with Optical Modulation of Schottky Barriers. <i>ACS Applied Nano Materials</i> , <b>2018</b> , 1, 6874-6881	5.6	14
16	In Situ Atomic-Level Studies of Gd Atom Release and Migration on Graphene from a Metallofullerene Precursor. <i>ACS Nano</i> , <b>2018</b> , 12, 10439-10451	16.7	6
15	Inhomogeneous Strain Release during Bending of WS on Flexible Substrates. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 39177-39186	9.5	9
14	High-Performance Two-Dimensional Schottky Diodes Utilizing Chemical Vapour Deposition-Grown Graphene-MoS Heterojunctions. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 37258-37266	9.5	17
13	Oligomeric aminoborane precursors for the chemical vapour deposition growth of few-layer hexagonal boron nitride. <i>CrystEngComm</i> , <b>2017</b> , 19, 285-294	3.3	34
12	Distinguishing Lead and Molecule States in Graphene-Based Single-Electron Transistors. <i>ACS Nano</i> , <b>2017</b> , 11, 5325-5331	16.7	36
11	Hydrogen Addition for Centimeter-Sized Monolayer Tungsten Disulfide Continuous Films by Ambient Pressure Chemical Vapor Deposition. <i>Chemistry of Materials</i> , <b>2017</b> , 29, 4904-4911	9.6	36
10	Photoluminescence Segmentation within Individual Hexagonal Monolayer Tungsten Disulfide Domains Grown by Chemical Vapor Deposition. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 15005-15014	9.5	48
9	Field-Effect Control of Graphene-Fullerene Thermoelectric Nanodevices. <i>Nano Letters</i> , <b>2017</b> , 17, 7055-7061	11.5	41
8	Lateral Graphene-Contacted Vertically Stacked WS /MoS Hybrid Photodetectors with Large Gain. <i>Advanced Materials</i> , <b>2017</b> , 29, 1702917	24	87
7	Growth of Large Single-Crystalline Monolayer Hexagonal Boron Nitride by Oxide-Assisted Chemical Vapor Deposition. <i>Chemistry of Materials</i> , <b>2017</b> , 29, 6252-6260	9.6	46

6	Revealing Defect-State Photoluminescence in Monolayer WS <sub>2</sub> by Cryogenic Laser Processing. <i>ACS Nano</i> , <b>2016</b> , 10, 5847-55	16.7	72
5	Biexciton Formation in Bilayer Tungsten Disulfide. <i>ACS Nano</i> , <b>2016</b> , 10, 2176-83	16.7	46
4	Mixed multilayered vertical heterostructures utilizing strained monolayer WS <sub>2</sub> . <i>Nanoscale</i> , <b>2016</b> , 8, 2639-47	16.7	24
3	Electroluminescence Dynamics across Grain Boundary Regions of Monolayer Tungsten Disulfide. <i>ACS Nano</i> , <b>2016</b> , 10, 1093-100	16.7	26
2	Layer-dependent modulation of tungsten disulfide photoluminescence by lateral electric fields. <i>ACS Nano</i> , <b>2015</b> , 9, 2740-8	16.7	39
1	Uniformity of large-area bilayer graphene grown by chemical vapor deposition. <i>Nanotechnology</i> , <b>2015</b> , 26, 395601	3.4	17